

DESCRIPTION

Mitsubishi 2SA1368 is a silicon PNP epitaxial type transistor. It designed with high collector dissipation, high voltage.

Complementary with 2SC3438.

FEATURE

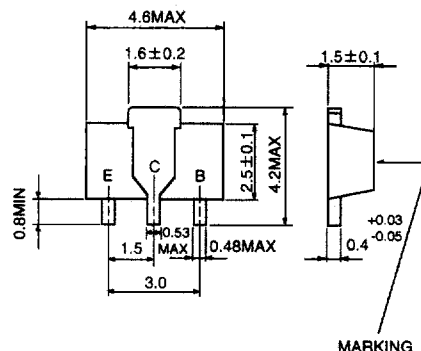
- High voltage $V_{CE0}=-100V$
- High collector current ($I_{CM}=-800mA$)
- High gain band width product $f_T=130MHz$ typ
- High collector dissipation $P_C=500mW$
- Small package for mounting

APPLICATION

Relay drive power supply etc.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

E : EMITTER
C : COLLECTOR EIAJ : SC-62
B : BASE JEDEC : -

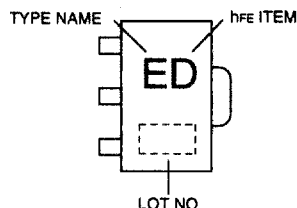
Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V_{CB0}	Collector to Base voltage	-100	V
V_{EB0}	Emitter to Base voltage	-5	V
V_{CE0}	Collector to Emitter voltage	-100	V
I_{CM}	Peak Collector current	-800	mA
I_C	Collector current	-500	mA
P_C	Collector dissipation(Ta=25°C)	500	mW
T_j	Junction temperature	+150	°C
T_{stg}	Storage temperature	-55 to +150	°C

MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

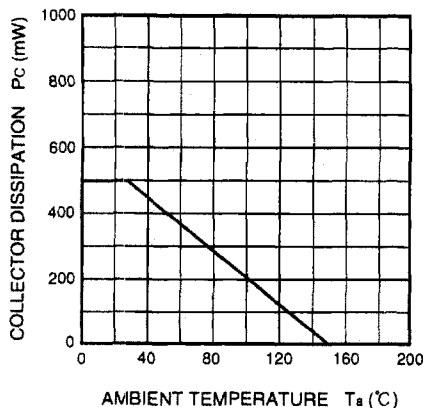
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=-10\mu A, I_E=0$	-100			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=-10\mu A, I_C=0$	-5			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=-1mA, R_{BE}=\infty$	-100			V
I_{CBO}	Collector cut off current	$V_{CB}=-50V, I_E=0$			-0.5	μA
I_{EBO}	Emitter cut off current	$V_{EB}=-2V, I_C=0$			-0.5	μA
h_{FE}^*	DC forward current gain	$V_{CE}=-10V, I_C=-10mA$	55		300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=-150mA, I_B=-15mA$		-0.15	-0.5	V
f_T	Gain band width product	$V_{CE}=-10V, I_E=10mA$		130		MHz
C_{ob}	Collector output capacitance	$V_{CB}=-10V, I_E=0, f=1MHz$		11		pF

* : It shows hFE classification in right table.

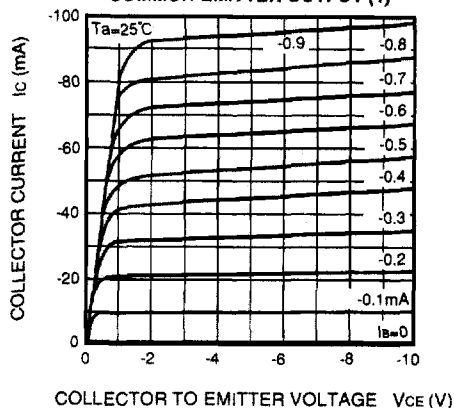
Marking	EC	ED	EE
hFE	55 to 110	90 to 180	150 to 300

TYPICAL CHARACTERISTICS

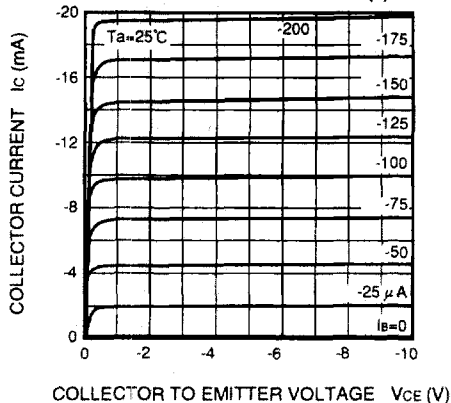
COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE



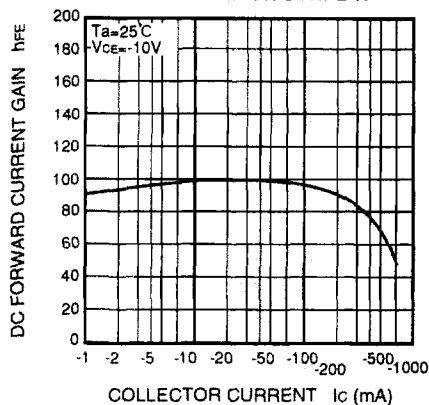
COMMON EMITTER OUTPUT (1)



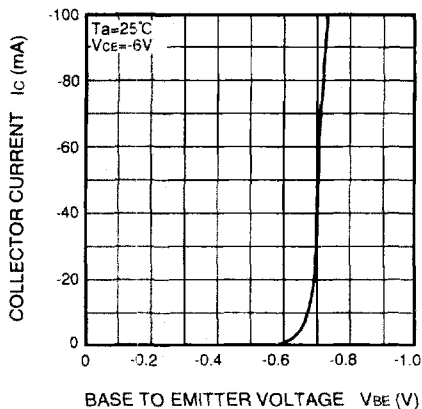
COMMON EMITTER OUTPUT (2)



DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT



COMMON EMITTER TRANSFER



GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT

